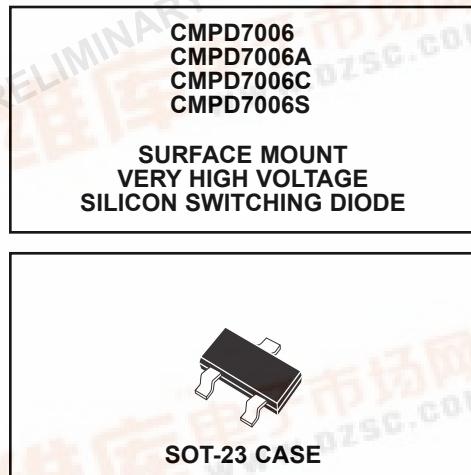


[查询CMPD7006供应商](#)

[捷多邦，专业PCB打样工厂，24小时加急出货](#)



The following configurations are available:

**CMPD7006** SINGLE  
**CMPD7006A** DUAL, COMMON ANODE  
**CMPD7006C** DUAL, COMMON CATHODE  
**CMPD7006S** DUAL, IN SERIES

**MARKING CODE: C7006**  
**MARKING CODE: C706A**  
**MARKING CODE: C706C**  
**MARKING CODE: C706S**

**MAXIMUM RATINGS PER DIODE: (TA=25°C)**

Continuous Reverse Voltage	VR	600	V
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	600	V
Continous Forward Current	I <sub>F</sub>	100	mA
Peak Repetitive Forward Current	I <sub>FRM</sub>	300	mA
Forward Surge Current, tp=1.0 μs	I <sub>FSM</sub>	4.0	A
Forward Surge Current, tp=1.0 s	I <sub>FSM</sub>	1.0	A
Power Dissipation	P <sub>D</sub>	350	mW
Operating and Storage			
Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>	357	°C/W

SYMBOL	UNITS
V <sub>R</sub>	V
V <sub>RRM</sub>	V
I <sub>F</sub>	mA
I <sub>FRM</sub>	mA
I <sub>FSM</sub>	A
I <sub>FSM</sub>	A
P <sub>D</sub>	mW
T <sub>J</sub> , T <sub>stg</sub>	°C
θ <sub>JA</sub>	°C/W

**ELECTRICAL CHARACTERISTICS PER DIODE: (TA=25°C unless otherwise noted)**

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>R</sub>	V <sub>R</sub> =480V		7.0	100	nA
I <sub>R</sub>	V <sub>R</sub> =480V, TA=150°C			100	μA
BV <sub>R</sub>	I <sub>R</sub> =1.0μA	600	675		V
V <sub>F</sub>	I <sub>F</sub> =10mA		0.88	1.0	V
V <sub>F</sub>	I <sub>F</sub> =50mA		1.04	1.2	V
V <sub>F</sub>	I <sub>F</sub> =100mA		1.16	1.4	V
C <sub>T</sub>	V <sub>R</sub> =0V, f=1.0 MHz			5.0	pF
t <sub>rr</sub>	I <sub>R</sub> =I <sub>F</sub> =10mA, R <sub>L</sub> =100Ω, Rec. to 1.0mA			500	ns

R0 (8-December 2003)

**Central**™  
Semiconductor Corp.

**DESCRIPTION:**

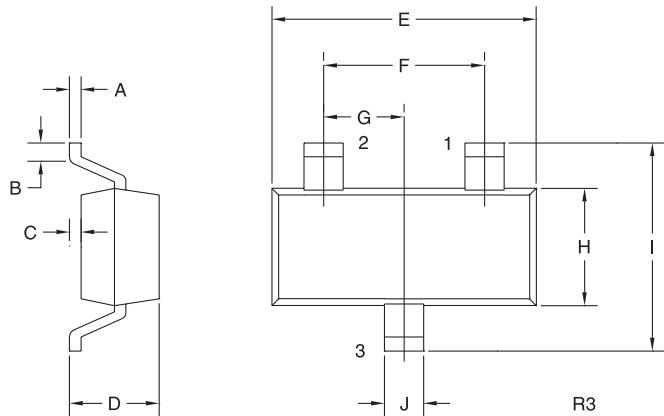
The Central Semiconductor CMPD7006, CMPD7006A, CMPD7006C and CMPD7006S are silicon switching diodes with various diode configurations, manufactured by the epitaxial planar process and packaged in an epoxy molded SOT-23 surface mount case. These devices are designed for applications requiring high voltage switching diodes.

**Central**<sup>TM</sup>  
Semiconductor Corp.

PRELIMINARY  
CMPD7006  
CMPD7006A  
CMPD7006C  
CMPD7006S

**SURFACE MOUNT  
VERY HIGH VOLTAGE  
SILICON SWITCHING DIODE**

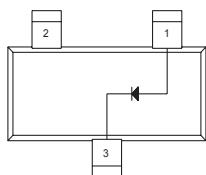
**SOT-23 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES	MILLIMETERS	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075	-	1.90	-
G	0.037	-	0.95	-
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

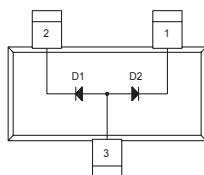
**MARKING CODE:  
SEE PREVIOUS PAGE**



**LEAD CODE:**

**CMPD7006**

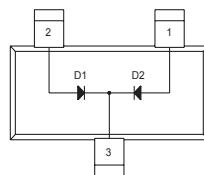
- 1) Anode
- 2) No Connection
- 3) Cathode



**LEAD CODE:**

**CMPD7006A**

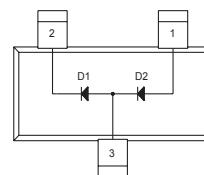
- 1) Cathode D2
- 2) Cathode D1
- 3) Anode D1, Anode D2



**LEAD CODE:**

**CMPD7006C**

- 1) Anode D2
- 2) Anode D1
- 3) Cathode D1, Cathode D2



**LEAD CODE:**

**CMPD7006S**

- 1) Anode D2
- 2) Cathode D1
- 3) Anode D1, Cathode D2

R0 (8-December 2003)